

3.3 V Dual Differential LVPECL/LVDS/CML to LVTTL/LVCMOS Translator

MC100EPT23

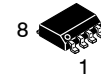
Description

The MC100EPT23 is a dual differential LVPECL/LVDS/CML to LVTTL/LVCMOS translator. Because LVPECL (Positive ECL), LVDS, and positive CML input levels and LVTTL/LVCMOS output levels are used, only + 3.3 V and ground are required. The small outline 8-lead SOIC package and the dual gate design of the EPT23 makes it ideal for applications which require the translation of a clock or data signal.

The EPT23 is available in only the ECL 100K standard. Since there are no LVPECL outputs or an external V_{BB} reference, the EPT23 does not require both ECL standard versions. The LVPECL/LVDS inputs are differential. Therefore, the MC100EPT23 can accept any standard differential LVPECL/LVDS input referenced from a V_{CC} of + 3.3 V.

Features

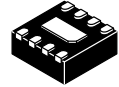
- 1.5 ns Typical Propagation Delay
- Maximum Operating Frequency > 275 MHz
- LVPECL/LVDS/CML Inputs, LVTTL/LVCMOS Outputs
- 24 mA LVTTL Outputs
- Operating Range:
 - ♦ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V with GND} = 0 \text{ V}$
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



SOIC-8 NB
D SUFFIX
CASE
751-07

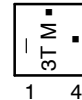
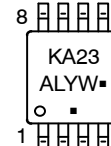
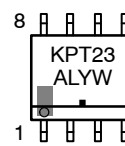


TSSOP-8
DT SUFFIX
CASE
948R-02



DFN-8
MN SUFFIX
CASE 506AA

MARKING DIAGRAMS*



- A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
M = Date Code
■ = Pb-Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note [AND8002/D](#).

ORDERING INFORMATION

Device	Package	Shipping [†]
MC100EPT23DG	SOIC-8 NB (Pb-Free)	98 Units/Tube
MC100EPT23DR2G	SOIC-8 NB (Pb-Free)	2500/Tape & Reel
MC100EPT23DTG	TSSOP-8 (Pb-Free)	100 Units/Tube
MC100EPT23DTR2G	TSSOP-8 (Pb-Free)	2500/Tape & Reel
MC100EPT23MNR4G	DFN-8 (Pb-Free)	1000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

MC100EPT23

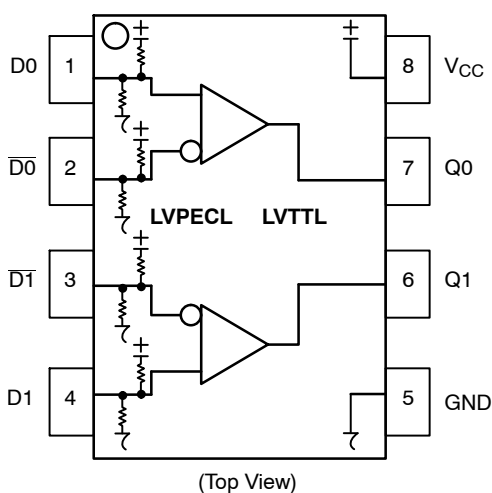


Figure 1. Logic Diagram and 8-Lead Pinout

Table 1. PIN DESCRIPTION

Pin	Function
Q0, Q1	LVTTTL/LVCMOS Outputs
D0**, D1** D0-bar**, D1-bar**	Differential LVPECL/LVDS/CML Inputs
V _{CC}	Positive Supply
GND	Ground
EP	(DFN-8 only) Thermal exposed pad must be connected to a sufficient thermal conduit. Electrically connect to the most negative supply (GND) or leave unconnected, floating open.

** Pins will default to $V_{CC}/2$ when left open.

Table 2. ATTRIBUTES

Characteristics	Value
Internal Input Pulldown Resistor	50 k Ω
Internal Input Pullup Resistor	50 k Ω
ESD Protection Human Body Model Machine Model Charged Device Model	> 1500 V > 100 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8 NB TSSOP-8 DFN-8	Level 1 Level 3 Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in
Transistor Count	91 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	

1. For additional information, see Application Note [AND8003/D](#).

MC100EPT23

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{CC}	Power Supply	GND = 0 V		3.8	V
V_I	Input Voltage	GND = 0 V	$V_I \leq V_{CC}$	3.8	V
I_{out}	Output Current	Continuous Surge		50 100	mA
T_A	Operating Temperature Range			-40 to +85	°C
T_{stg}	Storage Temperature Range			-65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 NB	190 130	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP-8	185 140	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	DFN-8	129 84	°C/W
T_{sol}	Wave Solder (Pb-Free)	<2 to 3 sec @ 260°C		265	°C
θ_{JC}	Thermal Resistance (Junction-to-Case)	(Note 1)	DFN-8	35 to 40	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. JEDEC standard multilayer board – 2S2P (2 signal, 2 power)

MC100EPT23

Table 4. PECL DC CHARACTERISTICS ($V_{CC} = 3.3\text{ V}$, $GND = 0\text{ V}$ (Note 2))

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{CCH}	Power Supply Current (Outputs set to HIGH)	10	20	35	10	20	35	10	20	35	mA
I_{CCL}	Power Supply Current (Outputs set to LOW)	15	27	40	15	27	40	15	27	40	mA
V_{IH}	Input HIGH Voltage	2075		2420	2075		2420	2075		2420	mV
V_{IL}	Input LOW Voltage	1355		1675	1355		1675	1355		1675	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Note 3)	1.2		3.3	1.2		3.3	1.2		3.3	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current D $\bar{D}$	-150 -150			-150 -150			-150 -150		0.5	μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lpm.

2. All values vary 1:1 with V_{CC} .

3. V_{IHCMR} min varies 1:1 with V_{EE} , V_{IHCMR} max varies 1:1 with V_{CC} . The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 5. LVTTTL/LVC MOS OUTPUT DC CHARACTERISTICS ($V_{CC} = 3.3\text{ V}$, $GND = 0.0\text{ V}$, $T_A = -40^\circ\text{C}$ to 85°C)

Symbol	Characteristic	Condition	Min	Typ	Max	Unit
V_{OH}	Output HIGH Voltage	$I_{OH} = -3.0\text{ mA}$	2.4			V
V_{OL}	Output LOW Voltage	$I_{OL} = 24\text{ mA}$			0.5	V
I_{OS}	Output Short Circuit Current		-180		-50	mA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lpm.

Table 6. AC CHARACTERISTICS ($V_{CC} = 3.0\text{ V}$ to 3.6 V , $GND = 0.0\text{ V}$ (Note 4))

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
$f_{\max}$	Maximum Frequency (Figure 2)	275	350		275	350		275	350		MHz
t_{PLH} , t_{PHL}	Propagation Delay to Output Differential (Note 5)	1.1	1.5	1.8	1.1	1.5	1.8	1.1	1.5	1.8	ns
t_{SK+} + t_{SK-} - t_{SKPP}	Output-to-Output Skew++ Output-to-Output Skew-- Part-to-Part Skew (Note 6)		15 35 70	60 80 500		15 40 70	70 80 500		30 40 140	125 80 500	ps
t_{JITTER}	Random Clock Jitter (RMS) (Figure 2)		5	10		5	10		5	10	ps
V_{PP}	Input Voltage Swing (Differential Configuration)	150	800	1200	150	800	1200	150	800	1200	mV
t_r , t_f	Output Rise/Fall Times (0.8 V – 2.0 V) Q, $\bar{Q}$	330	600	900	330	600	900	330	650	900	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lpm.

4. Measured with a 750 mV 50% duty-cycle clock source. $R_L = 500\ \Omega$ to GND and $C_L = 20\text{ pF}$ to GND. Refer to Figure 3.

5. Reference ($V_{CC} = 3.3\text{ V} \pm 5\%$; $GND = 0\text{ V}$)

6. Skews are measured between outputs under identical conditions.

MC100EPT23

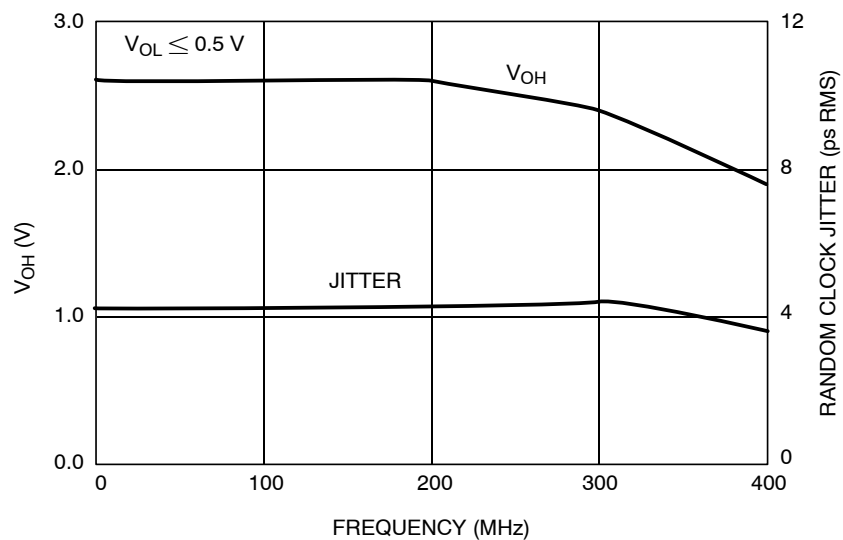


Figure 2. Typical V_{OH} / Jitter Versus Frequency (25°C)

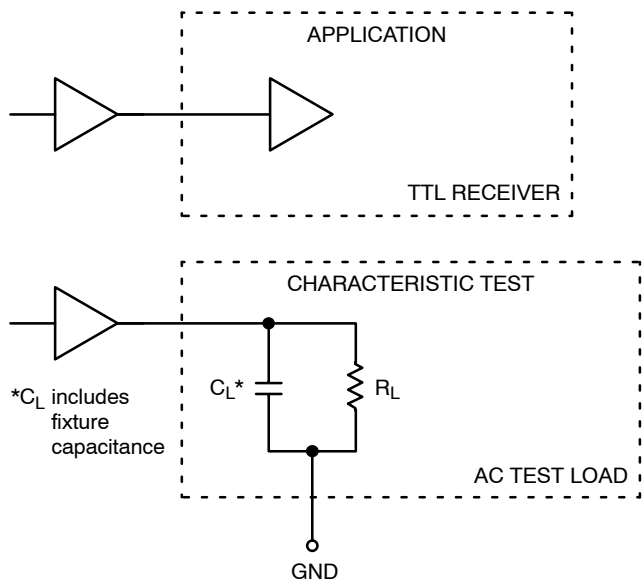


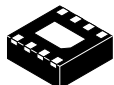
Figure 3. TTL Output Loading Used for Device Evaluation

MC100EPT23

Resource Reference of Application Notes

- AN1405/D** – ECL Clock Distribution Techniques
- AN1406/D** – Designing with PECL (ECL at +5.0 V)
- AN1503/D** – ECLinPS™ I/O SPICE Modeling Kit
- AN1504/D** – Metastability and the ECLinPS Family
- AN1568/D** – Interfacing Between LVDS and ECL
- AN1672/D** – The ECL Translator Guide
- AND8001/D** – Odd Number Counters Design
- AND8002/D** – Marking and Date Codes
- AND8020/D** – Termination of ECL Logic Devices
- AND8066/D** – Interfacing with ECLinPS
- AND8090/D** – AC Characteristics of ECL Devices

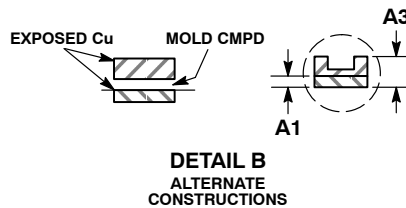
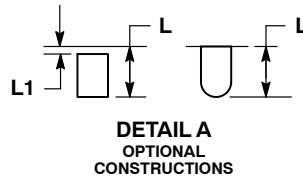
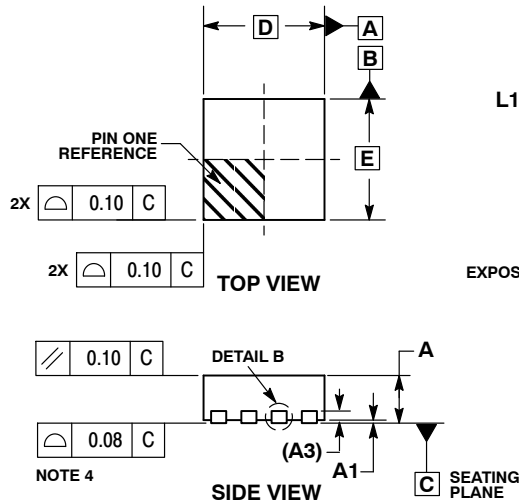
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SCALE 4:1

DFN8 2x2, 0.5P
CASE 506AA
ISSUE F

DATE 04 MAY 2016

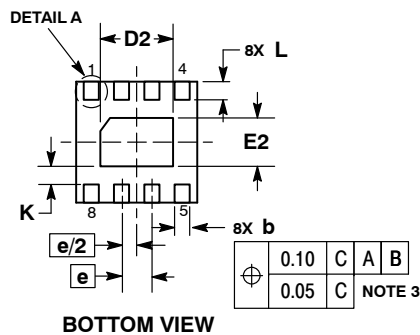
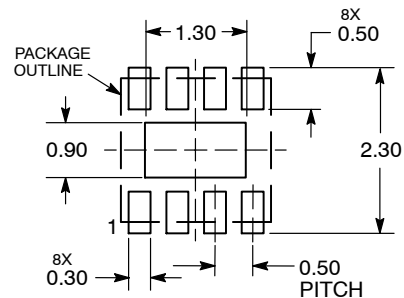


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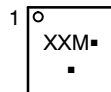
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

MILLIMETERS		
DIM	MIN	MAX
A	0.80	1.00
A1	0.00	0.05
A3	0.20	REF
b	0.20	0.30
D	2.00	BSC
D2	1.10	1.30
E	2.00	BSC
E2	0.70	0.90
e	0.50	BSC
K	0.30	REF
L	0.25	0.35
L1		0.10

RECOMMENDED SOLDERING FOOTPRINT*



GENERIC MARKING DIAGRAM*



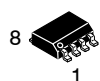
XX = Specific Device Code
M = Date Code
▪ = Pb-Free Device

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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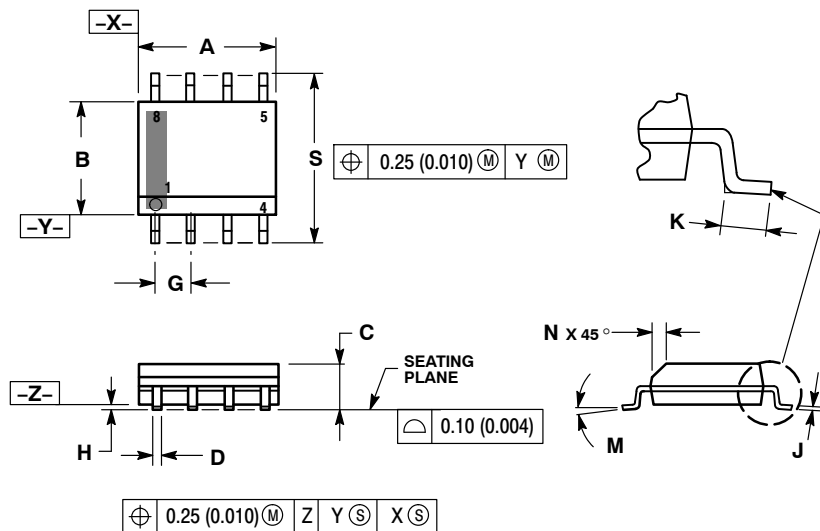
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SCALE 1:1

SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011

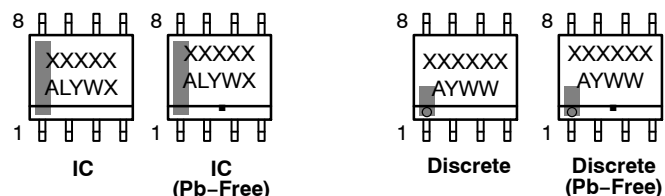
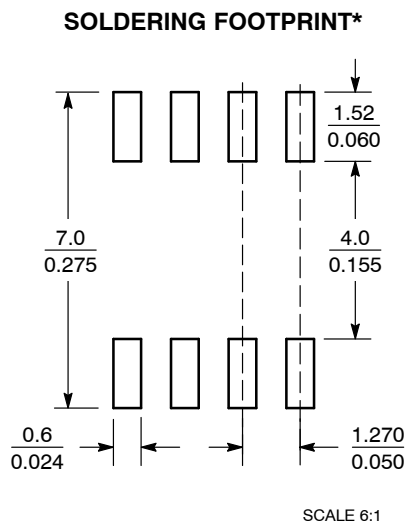


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

GENERIC
MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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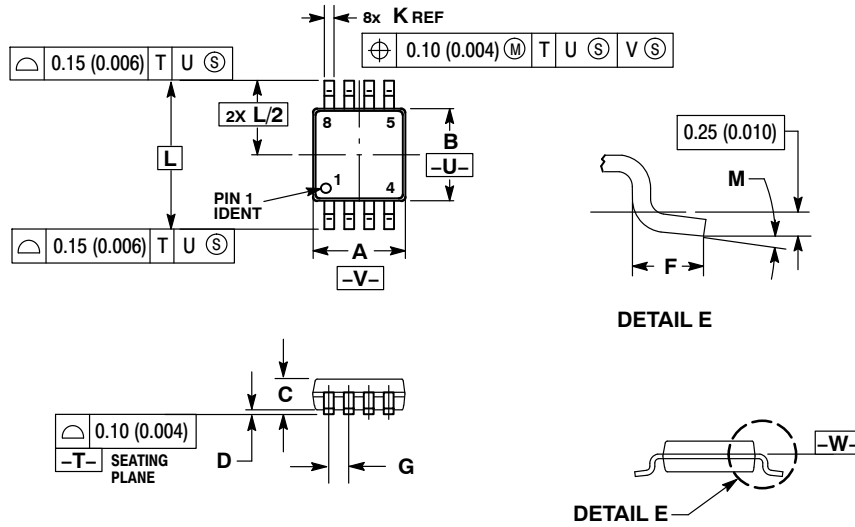
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SCALE 2:1

TSSOP-8 3.00x3.00x0.95
CASE 948R-02
ISSUE A

DATE 07 APR 2000



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	2.90	3.10	0.114	0.122
C	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65 BSC		0.026 BSC	
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193 BSC	
M	0°	6°	0°	6°

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DESCRIPTION:	TSSOP-8 3.00x3.00x0.95	PAGE 1 OF 1

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